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***TPS40002/3 Controllers Enable  
Miniature Synchronous Step-Down  
Converter for Low Logic Voltages,  
(PR070)***

***Reference Design***



## 2 Design Procedure

### 2.1 TPS4000X Family Device Selection

The TPS4000X family of devices offers four selections to encompass the frequency and output current mode choices. The TPS40003 is selected for two major factors. First, the internal oscillator components set a fixed switching frequency of 600kHz. This allows minimally sized filter components in this compact design. The second choice related to the TPS4000X family involves the selection of discontinuous current mode (DCM) operation or continuous current mode (CCM) operation at lighter loads. In this design, the TPS40003 is selected to keep the current continuous all the way to zero load, providing robust control characteristics.

### 2.2 Inductance Value

The output inductor value is selected to set the ripple current to a value most suited to overall circuit functionality. The inductor value is calculated by equation (1).

$$L_{\text{MIN}} = \frac{V_{\text{OUT}}}{f \times I_{\text{RIPPLE}}} \left( 1 - \frac{V_{\text{OUT}}}{V_{\text{IN(max)}}} \right) \quad (1)$$

in which  $I_{\text{RIPPLE}}$  is chosen to be 25% of  $I_{\text{OUT}}$ , or 1 A in this equation. This calculates to a value of 1.3  $\mu\text{H}$ , and a common value of 1  $\mu\text{H}$  is selected because a lower value usually has larger conductors to reduce power losses.

### 2.3 Input Capacitor Selection

Bulk input capacitor selection is based on allowable input voltage ripple and required RMS current carrying capability. In typical buck converter applications, the converter is fed from an upstream power converter with its own output capacitance. In this converter, an onboard capacitor is provided to supply the current required during the top MOSFET on-time while keeping ripple within acceptable limits. For this power level, input voltage ripple of 150 mV is reasonable, and the minimum capacitance is calculated in equation (2).

$$C = \frac{I \times \Delta t}{\Delta V} = \frac{5 \text{ A} \times 606 \text{ ns}}{0.15 \text{ V}} = 20 \mu\text{F} \quad (2)$$

To meet this requirement with the lowest size and cost, a single 22- $\mu\text{F}$ , X5R ceramic capacitor might be considered. Although these capacitors have an extremely small resistance, the datasheet indicates that the part undergoes a 30°C temperature rise with 2  $A_{\text{RMS}}$  current at 500 kHz. With  $V_{\text{IN}} = 3.0 \text{ V}$ , our circuit requires nearly 2  $A_{\text{RMS}}$  of current, so for a conservative design two capacitors are selected to allow for current derating. These capacitors function as power bypass components and should be located near the MOSFET package, to keep the high-frequency current flow in a tight loop. The low impedance characteristics of the dual ceramic capacitors help to reduce noise on the  $V_{\text{DD}}$  supply of the device. Specifically, the high-side MOSFET current sense is referenced to this point, so noise at the device must be kept to a low level.

## 2.4 Output Capacitor Selection

Selection of the output capacitor is based on many application variables, including function, cost, size, and availability. The minimum allowable output capacitance is determined by the amount of inductor ripple current and the allowable output ripple, as given in equation (3).

$$C_{\text{OUT(min)}} = \frac{I_{\text{RIPPLE}}}{8 \times f \times V_{\text{RIPPLE}}} \quad (3)$$

In this design,  $C_{\text{OUT(min)}}$  is 17  $\mu\text{F}$  with  $V_{\text{RIPPLE}} = 12 \text{ mV}$  to allow for some margin. However, this only affects the capacitive component of the ripple voltage. In addition, the voltage component due to the capacitor ESR must be considered, as given in equation (4).

$$C_{\text{ESR}} \leq \frac{V_{\text{RIPPLE}}}{I_{\text{RIPPLE}}} \quad (4)$$

For compactness while maintaining transient response capability, two 22- $\mu\text{F}$  ceramic capacitors are fitted in parallel. The total ESR of these capacitors is below 3  $\text{m}\Omega$ , and contributes only a few millivolts to the output voltage ripple.

## 2.5 MOSFET Selection

The small physical size of this design requires the use of a single SO-8 package which contains dual N-channel MOSFETs. The  $R_{\text{DS(on)}}$  for the MOSFETs is selected to be 16  $\text{m}\Omega$  to keep the conduction losses to a manageable amount at full load.

## 2.6 Short Circuit Protection

The TPS40003 implements short circuit protection by comparing the voltage across the topside MOSFET while it is on to a voltage dropped from VDD by  $R_{\text{LIM}}$  due to an internal current source of 15  $\mu\text{A}$  inside pin 1. Due to tolerances in the current source and variations in the power MOSFET on-voltage versus temperature, the short circuit level can only protect against gross overcurrent conditions, and should be set larger than rated load. In this particular case,  $R_{\text{LIM}}$  is selected in equation (5).

$$R_{\text{LIM}} = R1 = \frac{3 \times (I_{\text{OUT}}) \times R_{\text{DS(on)}}}{15 \mu\text{A}} \quad (5)$$

For this design,  $R_{\text{LIM}} = 15 \text{ k}\Omega$ , and the factor of 3 in the equation accounts for the variations in component tolerances and output current ripple. The high currents that are switched under short circuit conditions may cause SW pin 8 to be driven below ground several volts, possibly injecting substrate current which can cause improper operation of the device. A 3.3- $\Omega$  resistor has been placed in series with this pin to limit its excursion to safe levels.

## 2.7 Compensation Design

The TPS40003 uses voltage mode control in conjunction with a high frequency error amplifier. For the fastest transient response, the loop crossover frequency is set at  $1/10 f_S$ , or 60 kHz. The power circuit L-C double pole corner frequency  $f_C$  is situated at 24 kHz, and the output capacitor ESR zero is way out of the picture above 1 MHz. The feedback compensation network is implemented to provide two zeroes and three poles. The first pole is placed at the origin to improve dc regulation.

The first zero is placed at approximately  $2/3 f_C$ , 18 kHz,

$$f_{z1} = \frac{1}{2 \times \pi \times R_3 \times C_{10}} \tag{6}$$

The second zero is selected at  $f_C$ ,

$$f_{z2} = \frac{1}{2 \times \pi \times (R_4 + R_6) \times C_{11}} \tag{7}$$

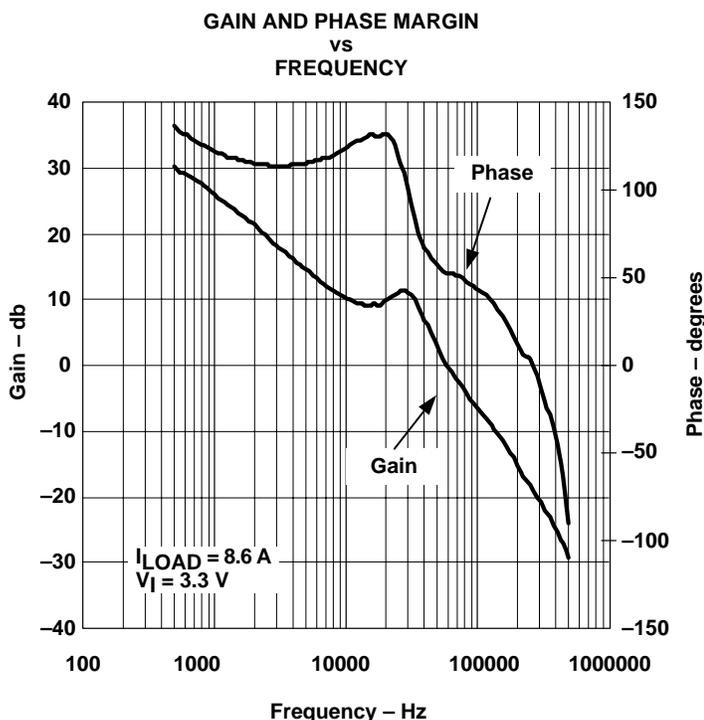
The two poles are placed at one-half the switching frequency,

$$f_{p1} = \frac{1}{2 \times \pi \times R_3 \times \left( \frac{C_9 \times C_{10}}{C_9 + C_{10}} \right)} \tag{8}$$

and

$$f_{p2} = \frac{1}{2 \times \pi \times R_6 \times C_{11}} \tag{9}$$

Figure 2 shows the plots for the closed loop gain and phase with  $V_{IN} = 3.3$  V and  $I_{OUT} = 4.4$  A. At the crossover frequency of 60 kHz the phase margin is approximately 51 degrees.



**Figure 2. Gain and Phase Plot with 2.2-A Load**

## 2.8 Snubber Component Selection

The switch node where Q1 and L1 come together is very noisy. An R-C network fitted between this node and ground can help reduce ringing and voltage overshoot on Q1:B. This ringing noise should be minimized to prevent it from confusing the control circuitry which is monitoring this node for current limit, Predictive Gate Drive™, and DCM control functions.

As a starting point, the snubber capacitor C8 is generally chosen to be five to eight times larger than the parasitic capacitance at the node, which is primarily C<sub>OS</sub> of Q1:B. Since C<sub>OS</sub> is 440 pF for Q1:B, C8 is chosen to be 3.3 nF. R2 is empirically determined to be 2.2 Ω, which minimizes the ringing and overshoot at the switch node. With low input voltages the power loss,  $\frac{1}{2} CV^2f$ , is relatively small at 24 mW.

## 3 PowerPAD Packaging

The TPS4000X family is available in the DGQ version of TI's PowerPAD™ thermally enhanced package. In the PowerPAD™, the integrated circuit die is attached to the leadframe die pad using a thermally conductive epoxy. The leadframe die pad is exposed on the bottom side of the package, and can be soldered to the PCB using standard solder flow techniques when maximum heat dissipation is required. However, in many applications the PowerPAD™ does NOT have to be soldered to the PCB.

The PowerPAD™ package helps to keep the junction temperature rise relatively low even with the power dissipation inherent in the onboard MOSFET drivers. This power loss is proportional to switching frequency, drive voltage, and the gate charge needed to enhance the N-channel MOSFETs. Effective heat removal allows the use of ultra small packaging while maintaining high component reliability.

To effectively remove heat from the PowerPAD™ package, a thermal land should be provided directly underneath the package whether the package needs to be soldered or not. This thermal land usually has vias that help to spread heat to internal copper layers and/or the opposite side of the PCB. The vias should not have thermal reliefs that are often used on ground planes, because this would reduce the copper area to transfer heat. Additionally, the vias should be small enough so that the holes are effectively plugged when plated. This prevents the solder from wicking away from the connection between the PCB surface and the bottom of the part. A typical construction would utilize a few vias of 0.013" diameter plated with 1 ounce copper in the land under the TPS40003. A typical layout pattern is shown in Figure 3, but does not show the copper land which would encompass the vias above and below the device.

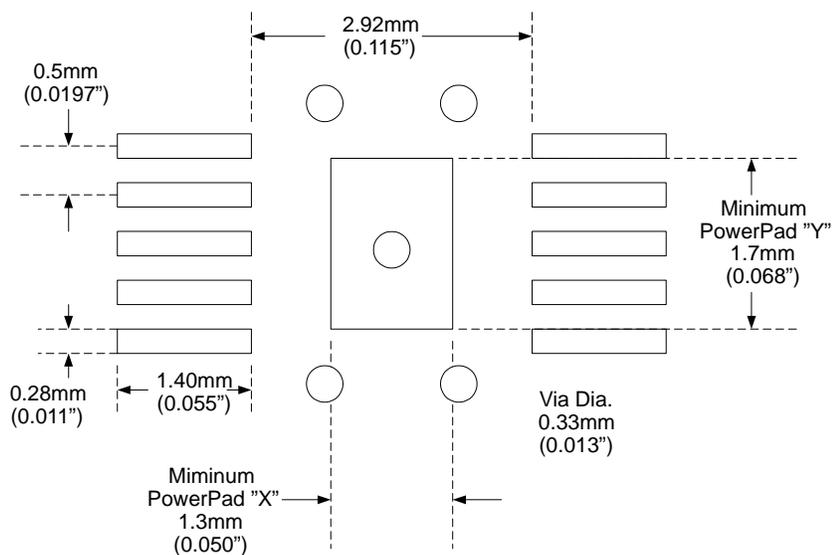
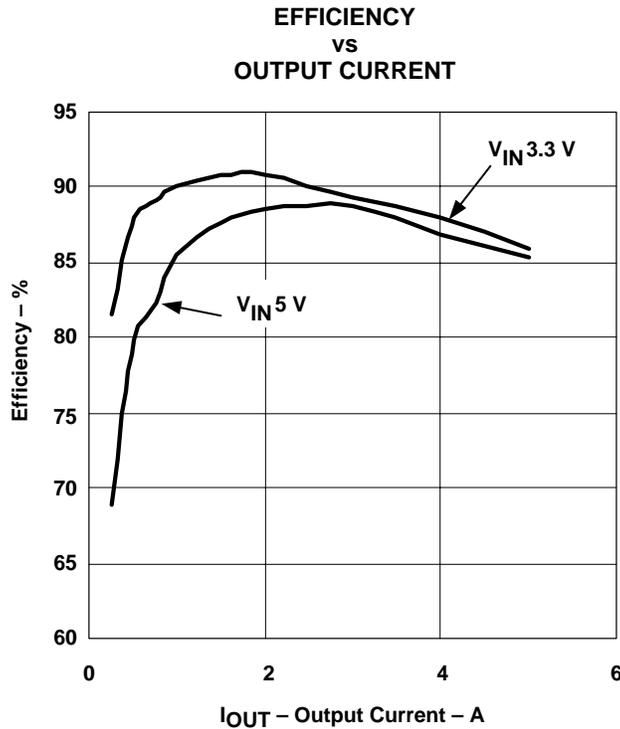


Figure 3. PowerPAD PCB Layout Guidelines

The document, *PowerPAD Thermally Enhanced Package Application Report* (TI Literature Number SLMA002) should be consulted for more information on the PowerPAD™ package. This report offers in-depth information on the package, assembly and rework techniques, and illustrative examples of the thermal performance of the PowerPAD™ package.

## 4 Test Results/Performance Data

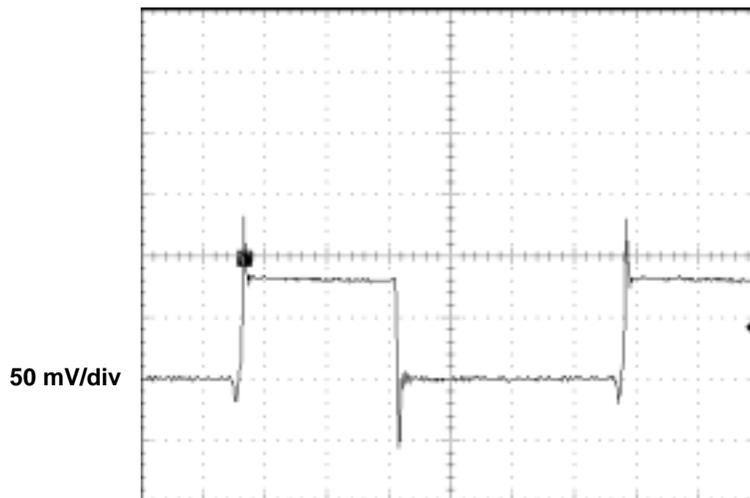
Typical efficiency curves are shown in Figure 4 for an input of 3.3 V and 5 V.



**Figure 4.**

Figure 5 shows the switch node during typical operation at full load. Note that there is very minimal body diode conduction in the bottom MOSFET. This is a result of using the Predictive Delay™ control implementation. This technique is able to dynamically change the delays in the MOSFET drive circuit to account for variations in line, load, and between devices.

**TYPICAL SWITCH NODE WAVEFORM**

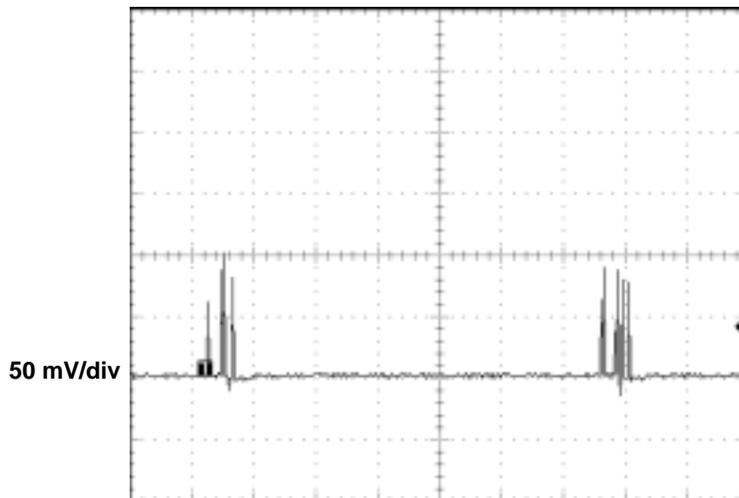


t – Time – 50  $\mu$ s/div

**Figure 5.**

Circuit operation with an output short circuit is shown in Figure 6. After each restart into a short circuit the pulses terminate for a period of approximately six milliseconds. This causes the input power to collapse to minuscule levels, and the circuit is protected.

**SHORT CIRCUIT OPERATION**

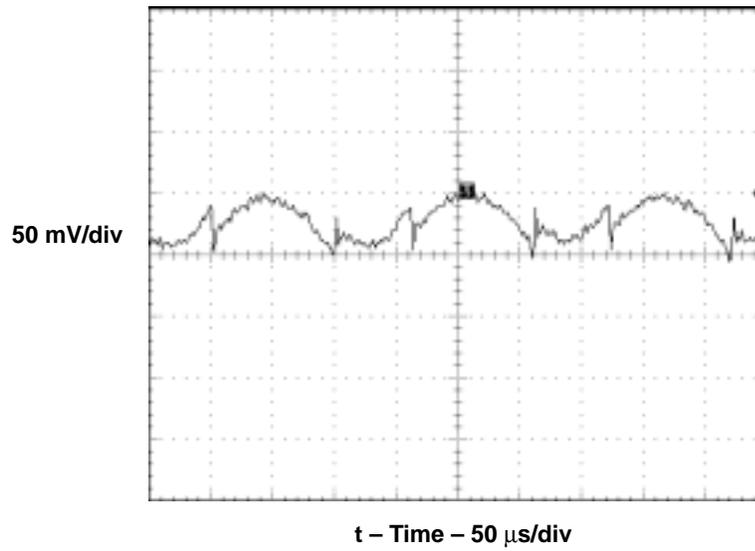


t – Time – 50  $\mu$ s/div

**Figure 6.**

The output ripple is well within the 24-mV limit, as shown in Figure 7.

**OUTPUT VOLTAGE RIPPLE**



**Figure 7.**

## 5 PCB Layout

All the PCB layout information is available in Gerber or PCAD format.

## 6 List of Material

Table 1 lists the components used in this design. With minor component tweaks this design could be modified to meet a wide range of applications.

	Reference	Qty	Description	Manufacturer	Part Number
Capacitor	C1, C4, C12, C13	4	Ceramic, 22 $\mu$ F, 6.3 V, X5R, 20%, 1210		
	C10	1	Ceramic, 0.001 $\mu$ F, 50 V, X7R, 10%, 603		
	C11	1	Ceramic, 470 pF, 50 V, X7R, 10%, 603		
	C5	1	Ceramic, 0.0047 $\mu$ F, 50 V, X7R, 10%, 603		
	C6,7	2	Ceramic, 1 $\mu$ F, 10 V, X5R, 10%, 805		
	C8	1	Ceramic, 0.0033 $\mu$ F, 50 V, X7R, 10%, 805		
	C9	1	Ceramic, 68 pF, 50 V, NPO, 10%, 603		
Jumper	J1, J2	2	2-pin, 15 A, 5.1 mm, 148830	OST	ED1609
Inductor	L1	1	SMT, 1.0 $\mu$ H, 8.5 A, 10 m $\Omega$ , 0.270 sq	Vishay	IHLP-2525CZ-01 1 $\mu$ H, 20%
MOSFET	Q1	1	Dual N-channel, 20 V, 9.4 A, 18 m $\Omega$ , SO8	Fairchild	FDS6898A
Resistor	R1	1	Chip, 15 k $\Omega$ , 1/16 W, 1%, 603	Std	Std
	R2	1	Chip, 2.2 $\Omega$ , 1/10 W, 5%, 805	Std	Std
	R3	1	Chip, 8.66 k $\Omega$ , 1/16 W, 1%, 603	Std	Std
	R4	1	Chip, 12.1 k $\Omega$ , 1/16 W, 1%, 603	Std	Std
	R5	1	Chip, 16.9 k $\Omega$ , 1/16 W, 1%, 603	Std	Std
	R6	1	Chip, 1 k $\Omega$ , 1/16 W, 1%, 603	Std	Std
	R7	1	Chip, 3.3 $\Omega$ , 1/16 W, 5%, 603	Std	Std
JACK	TP1, TP2, TP3, TP4, TP5	5	Test Point, Clr	Farnell	240-3xx
Adaptor	TP6	1	3.5-mm probe clip ( or 131-5031-00), 72900	Tektronix	131-4244-00
Device	U1	1	Low Input Voltage Mode, Sync. Buck Controller, DGQ10	TI	TPS40003DGQ

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